



DMN3200U

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
 - 90 m Ω @ V_{GS} = 4.5V
 - 110 m Ω @ $V_{GS} = 2.5V$
 - 200 m Ω @ $V_{GS} = 1.5V$
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- **ESD Protected Gate**
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2, 3 and 5)
- Qualified to AEC-Q101 Standards for High Reliability



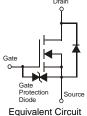
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

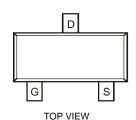
SOT-23





TOP VIEW





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±8	V
Drain Current (Note 1)	I _D	2.2	А
Pulsed Drain Current (Note 1)	I _{DM}	9	А

Thermal Characteristics @TA = 25°C unless otherwise specified

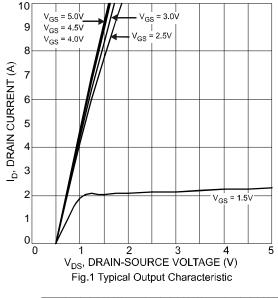
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_{D}	650	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	192	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μА	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±5	μА	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(th)}$	0.45		1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
	R _{DS (ON)}		62 70 150	90		$V_{GS} = 4.5V, I_D = 2.2A$	
Static Drain-Source On-Resistance				110 200	mΩ	$V_{GS} = 2.5V, I_D = 2A$	
						$V_{GS} = 1.5V, I_D = 0.67A$	
Forward Transfer Admittance	Y _{fs}	_	5	_	S	$V_{DS} = 5V, I_D = 2.2A$	
Diode Forward Voltage (Note 4)	V_{SD}	_	_	0.9	V	$V_{GS} = 0V, I_S = 1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}	_	290	_	pF	1/ 40// 1/ 01/	
Output Capacitance	Coss	_	66	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		35	_	pF	1 - 1.000112	

- 1. Device mounted on FR-4 PCB, on minimum recommended pad layout on 2oz. Copper pads.
- 2. No purposefully added lead. Halogen and Antimony Free.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 4. Short duration pulse test used to minimize self-heating effect.
- 5. Product manufactured with Green Molding Compound and does not contain Halogens or Sb₂O₃ Fire Retardants.





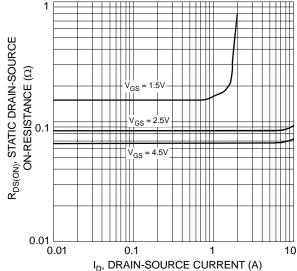


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

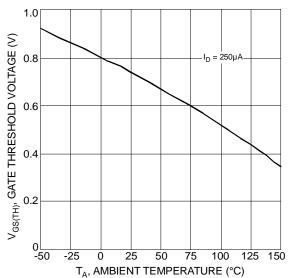
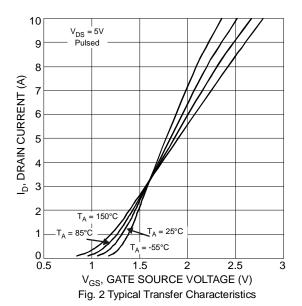


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



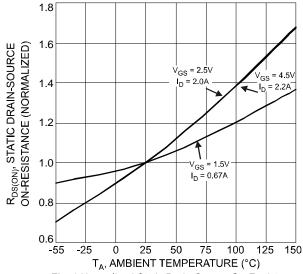
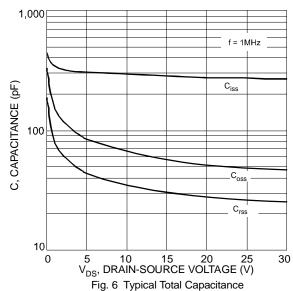


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





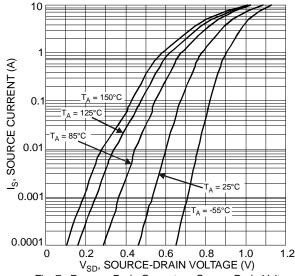


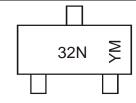
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Ordering Information (Note 6)

Part Number	Case	Packaging
DMN3200U-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

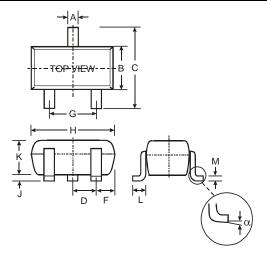


32N = Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key

Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	ι	J	\	/	V	٧)	Κ	`	1	Ž	7
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

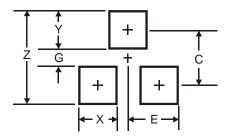
Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
H	2.80	3.00			
7	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Dimensions in mm					



Suggested Pad Layout



1	
Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Υ	1.4
С	2.0
E	0.9

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